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Attorney Docket No. FUJ 99228 CIP
Client Matter No. 80458.0011
Express Mail No.: EV035493725US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Katsuyoshi Matsuura et al.

Serial No. 09/551,233

Filed: April 17, 2000

For: SEMICONDUCTOR DEVICE HAVING A
FERROELECTRIC CAPACITOR AND A
FABRICATION PROCESS THEREOF

Examiner: Lee, Hsien Ming

Art Unit: 2823

Confirmation No.: 9686

AMENDMENT AND RESPONSE PURSUANT TO OFFICE ACTION
DATED JUNE 19, 2002

BOX FEE AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the office communication mailed June 19, 2002, please amend the application as follows:

IN THE CLAIMS:

Please cancel claim 13, without prejudice.

Please amend claims 12, 14, and 15 to read as follows:

12. (Amended) A method of fabricating a semiconductor device having a ferroelectric capacitor, comprising the steps of:

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forming an active device element on a substrate;
forming an insulation film over said substrate to cover said active device element;

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